

Plasma Physics

PART A1: INTRODUCTION TO PLASMA SCIENCE

I. What is a plasma? 1

II. Plasma fundamentals 3

1. Quasineutrality and Debye length
2. Plasma frequency and acoustic velocity
3. Larmor radius and cyclotron frequency
4. $E \times B$ drift
5. Sheaths and presheaths

PART A2: INTRODUCTION TO GAS DISCHARGES

III. Gas discharge fundamentals 11

1. Collision cross section and mean free path
2. Ionization and excitation cross sections
3. Coulomb collisions; resistivity
4. Transition between neutral- and ion-dominated electron collisions
5. Mobility, diffusion, ambipolar diffusion
6. Magnetic field effects; magnetic buckets

Cross section data 21

PART A3: PLASMA SOURCES I

IV. Introduction to plasma sources 25

1. Desirable characteristics of plasma processing sources
2. Elements of a plasma source

PART A4: PLASMA SOURCES II

V. RIE discharges 31

1. Debye sheath
2. Child-Langmuir sheath
3. Applying a DC bias
4. Applying an RF bias
5. Displacement current
6. Ion dynamics in the sheath
7. Other effects in RIE reactors
8. Disadvantages of RIE reactors
9. Modified RIE devices

Plasma Chemistry

PART B1: OVERVIEW OF PLASMA PROCESSING IN MICROELECTRONICS FABRICATION

I. Plasma processing 99

II. Applications in Microelectronics 100

PART B2: KINETIC THEORY AND COLLISIONS

I. Kinetic theory 103

II. Practical gas kinetic models and macroscopic properties 109

1. Maxwell-Boltzmann distribution (MBD)
2. A simplified gas model (SGM)
3. Energy content
4. Collision rate between molecules
5. Mean free path
6. Flux of gas particles on a surface
7. Gas pressure
8. Transport properties
9. Gas flow

III. Collision dynamics 119

1. Collision cross sections
2. Energy transfer
3. Inelastic collisions

PART B3: ATOMIC COLLISIONS AND SPECTRA

I. Atomic energy levels 125

II. Atomic collisions 126

1. Excitation processes
2. Relaxation and recombination processes

III. Elastic collisions 129

1. Coulomb collisions
2. Polarization scattering

IV. Inelastic collisions 130

1. Constraints on electronic transitions
2. Identification of atomic spectra
3. A simplified model

PART A5: PLASMA SOURCES III**VI. ECR sources 47****VII. Inductively coupled plasmas (ICPs) 49**

1. Overview of ICPs
2. Normal skin depth
3. Anomalous skin depth
4. Ionization energy
5. Transformer coupled plasmas (TCPs)
6. Matching circuits
7. Electrostatic chucks (ESCs)

PART A6: PLASMA SOURCES IV**VIII. Helicon wave sources and HDPs 61**

1. Dispersion relation
2. Wave patterns and antennas
3. Mode jumping
4. Modified skin depth
5. Trivelpiece-Gould modes
6. Examples of helicon measurements
7. Commercial helicon sources

IX. Discharge equilibrium 69

1. Particle balance
2. Energy balance
3. Electron temperature
4. Ion temperature

PART A7: PLASMA DIAGNOSTICS**X. Introduction 75****XI. Remote diagnostics 75**

1. Optical spectroscopy
2. Microwave interferometry
3. Laser Induced Fluorescence (LIF)

XII. Langmuir probes 79

1. Construction and circuit
2. The electron characteristic
3. Electron saturation
4. Space potential
5. Ion saturation current 83
6. Distribution functions 90
7. RF compensation
8. Double probes and hot probes

PART B4: MOLECULAR COLLISIONS AND SPECTRA**I. Molecular energy levels 137**

1. Electronic energy level
2. Vibrational energy level
3. Rotational energy level

II. Selection rule for optical emission of molecules 139**III. Electron collisions with molecules 140**

1. Frank-Condon principle
2. Dissociation
3. Dissociative ionization
4. Dissociative recombination
5. Dissociative electron attachment
6. Electron impact detachment
7. Vibrational and rotational excitation

IV. Heavy particle collisions 142**V. Gas phase kinetics 143****PART B5: PLASMA DIAGNOSTICS****I. Optical emission spectroscopy 151**

1. Optical emission
2. Spectroscopy
3. Actinometry
4. Advantages/disadvantages
5. Application: end-point detection

II. Laser induced fluorescence 161**III. Laser interferometry 162****IV. Full-wafer interferometry 163****V. Mass spectrometry 164****PART B6: PLASMA SURFACE KINETICS****I. Plasma chemistry 167****II. Surface reactions 167**

1. Spontaneous surface etching
2. Spontaneous deposition
3. Ion sputtering kinetics
4. Ion-enhanced chemical etching

III. Loading 177**IV. Selectivity 178****V. Detailed reaction modeling 179**

XIII. Other local diagnostics	93
1. Magnetic probes	
2. Energy analyzers	
3. RF current probe	
4. Plasma oscillation probe	
PART AB8: CURRENT PROBLEMS IN SEMICONDUCTOR PROCESSING	199
I. Front-end challenges	199
1. High-k dielectrics	
2. Metal gates	
II. Back-end challenges	201
1. Copper metallization	
2. Interlayer dielectrics (ILDs)	
3. Barrier materials	
III. Patterning nanometer features	204
1. E-beam	
2. Resist trimming	
IV. Deep reactive etch for MEMS	205
V. Plasma-induced damage	206
VI. Species control in plasma reactors	207

PART B7: FEATURE EVOLUTION AND MODELING

I. Fundamentals of feature evolution in plasma etching	183
II. Predictive modeling	185
III. Mechanisms of profile evolution	186
1. Ion bombardment directionality	
2. Ion scattering within the feature	
3. Deposition rate of passivants	
4. Line-of-sight redeposition of products	
5. Charging of surfaces in the features	
IV. Profile simulation	190
V. Plasma damage	193
1. Contamination	
2. Particulates	
3. Gate oxide Damage – photon	
4. Gate oxide damage – electrical stress	
5. Lattice damage	
6. Post-etch corrosion	